

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:
  - a gate electrode formed over a substrate;
  - a gate insulating film formed over the gate electrode;
  - a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and
  - source and drain regions comprising silicon formed on said semiconductor film,wherein a peak position of a Raman spectrograph of said semiconductor film is ~~shifted to a lower wave number side from  $520\text{ cm}^{-1}$~~  lower than  $520\text{ cm}^{-1}$ .
2. (Original) The semiconductor device according to claim 1 wherein said gate electrode comprises molybdenum.
3. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide.
4. (Currently Amended) A semiconductor device comprising:
  - a gate electrode formed over a substrate;
  - a gate insulating film formed over the gate electrode;
  - a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and
  - source and drain regions comprising silicon formed on said semiconductor film,wherein a peak position of a Raman spectrograph of said semiconductor film is ~~shifted to a lower wavenumber side from  $520\text{ cm}^{-1}$~~  lower than  $520\text{ cm}^{-1}$  and said semiconductor film has a distortion in the lattice.

5. (Original) The semiconductor device according to claim 4 wherein said gate electrode comprises molybdenum.

6. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide.

7. (Currently Amended) A semiconductor device comprising:  
a gate electrode formed over a substrate;  
a gate insulating film formed over the gate electrode;  
a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed therebetween, said semiconductor film including a channel formation region and  
source and drain regions comprising silicon formed on said semiconductor film,

wherein a peak position of a Raman spectrograph of said semiconductor film is ~~shifted to a lower wavenumber side from  $520\text{-cm}^{-1}$~~  lower than  $520\text{ cm}^{-1}$  and said semiconductor film has a distortion in the lattice, and the semiconductor film has no barrier against carriers at grain boundaries.

8. (Original) The semiconductor device according to claim 7 wherein said gate electrode comprises molybdenum.

9. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide.

10. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide containing fluorine.

11. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide containing fluorine.

12. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide containing fluorine.